



PTSMC-03-352

February 27, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/728,216 12/04/03 |

Hau Tao et al.

METHOD OF FORMING A FLOATING GATE
FOR A STACKED GATE FLASH MEMORY
DEVICE
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on March 1, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

SBAR 3/1/04

U.S. Patent 6,171,906 to Hsieh et al., "Method of Forming Sharp Beak of Poly to Improve Erase Speed in Split Gate Flash," discloses a split-gate flash device and method of manufacture.

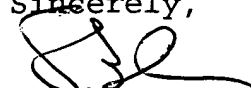
U.S. Patent 6,165,845 to Hsieh et al., "Method to Fabricate Poly Tip in Split-gate Flash," describes a split-gate flash device and method of manufacture.

U.S. Patent 6,479,859 to Hsieh et al., "Split Gate Flash Memory with Multiple Self-alignments," discloses a method for forming a split-gate flash memory cell where the floating gate of the cell is self-aligned to isolation, to source and to word line.

U.S. Patent 6,537,869 to Furuhashi, "Semiconductor Devices having a Non-volatile Memory Transistor and Methods for Manufacturing the Same," discloses a semiconductor device and a method for manufacturing the same.

U.S. Patent 6,528,844 to Hopper et al., "Split-gate Flash Memory Cell with a Tip in the Middle of the Floating Gate," discusses forming a split-gate FLASH memory cell with a floating gate that has a tip in the middle of the floating gate.

Sincerely,



Stephen B. Ackerman, Reg. #37761

Form PTO-1449

Information Disclosure Citation
in an Application

Use several sheets if necessary

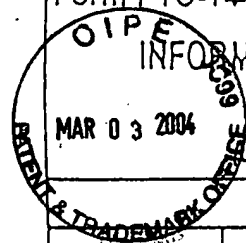
Docket Number (Specimen)
TSMC-03-352

Applicant
Hau Tao et al.

Filing Date
12/04/03

Application Number
10/728,216

Group Art Unit



U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE & APPROPRIATE
	6171906	1/9/01	Hsieh et al.	438	257	8/23/99
	6165845	12/26/00	Hsieh et al.	438	260	4/26/99
	6479859	11/12/02	Hsieh et al.	257	315	2/6/01
	6537869	3/25/03	Furuhata	438	239	9/15/00
	6528844	3/4/03	Hopper et al.	257	316	10/31/01

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant